Excess Idd after proton irradiation - summary

Module	Lot	Wafer	Idd_pre	Idd_post	Increase factor	Later measurements	
K4_205	Z34685	03	490 mA	805 mA (04/2001)	1.64		
UKK2	Z34685	03		855 mA			
KEK0	Z34685	05	470 mA	805 mA (10/2000)	1.71		
UKK1	Z34685	05	445 mA	655 mA (10/2000)	1.47		
VAL_166	Z34685	05	445 mA	620 mA (10/2000)	1.39	510 mA (11/2001)	
K3T1 (6 ch)	Z34685	05	230 mA	340 mA (08/2000)			
B017	Z34685A	20	440 mA	760 mA (04/2001)	1.72		
B020	Z36459A	03	475 mA	610 mA (04/2001)	1.28	485 mA (07/2001)	
K4_218	Z36459A	04	450 mA	1015 mA (05/2001)	2.25	975 mA (07/2001)	840 mA (08/2001)
B037	Z36459A	05	450 mA	1190 mA (04/2001)	2.64	980 mA (07/2001)	
B050	Z36459A	06	440 mA	1030 mA (07/2001)	2.34		
B047	Z38850	12	450 mA	780 mA (08/2001)	1.73	720 mA (10/2001)	
B044	Z38850	15	440 mA	640 mA (08/2001)	1.45	570 mA (10/2001)	

Idd_post - after 3×10^{14} p/cm^2 and 7 day annealing at 25 degree.